

In the Claims:

1. (Currently amended) An aqueous chemical mechanical planarizing composition comprising:
  - an oxidizer for promoting barrier removal;
  - an abrasive;
  - an inhibitor for decreasing removal of a metal interconnect; and
  - a water soluble polymaleic acid~~carboxylic acid polymer having at least one repeat unit of the polymer comprising at least two carboxylic acid functionalities~~ and wherein the chemical mechanical planarizing composition has a pH of less than 4 adjusted with an inorganic pH adjusting agent, the inorganic pH adjusting agent being an acid; and a tantalum nitride removal rate of at least eighty percent of copper removal rate at a pad pressure of 13.8 kPa.
2. (Currently amended) The composition of Claim 1, wherein the ~~carboxylic acid polymer~~polymaleic acid comprises a homopolymer or a copolymer.
3. Cancelled.
4. (Previously presented) The composition of Claim 1, having a pH of 1.5 to less than 4.
5. (Currently amended) An aqueous chemical mechanical planarizing composition comprising:
  - 0.05 to 15 wt% abrasive;
  - 0.1 to 10 wt% oxidizing agent;
  - 0.0025 to 2 wt% of benzotriazole; and
  - 0.01 to 5 wt% of a water soluble polymaleic acid~~carboxylic acid polymer, wherein at least one repeat unit of the polymer has at least two carboxylic acid functionalities~~, and wherein the pH of the chemical mechanical planarizing composition is less than 4 adjusted with an inorganic pH adjusting agent, the inorganic pH adjusting agent including an acid selected from nitric acid, sulfuric acid, hydrochloric acid and phosphoric acid; and a tantalum nitride removal rate of at least ninety percent of copper removal rate at a pad pressure of 13.8 kPa.
6. (Currently amended) The composition of Claim 5, wherein the ~~carboxylic acid polymer~~polymaleic acid comprises a homopolymer or a copolymer.

7. Cancelled.

8. (Withdrawn-currently amended) A method for planarizing a semiconductor wafer comprising:

applying an aqueous chemical mechanical planarizing composition to the wafer, wherein the composition comprises a water soluble polymaleic acid~~carboxylic acid~~ polymer having at least one repeat unit of the polymer comprising at least two carboxylic acid functionalities; an abrasive; an oxidizer for promoting barrier removal; and a corrosion inhibitor for limiting removal of the interconnect metal, wherein the chemical mechanical planarizing composition has a pH of less than 4 adjusted with an inorganic pH adjusting agent, the inorganic pH adjusting agent being an acid; and

polishing the semiconductor wafer, wherein the chemical mechanical planarizing composition has a tantalum nitride removal rate of at least eighty percent of copper removal rate at a pad pressure of 13.8 kPa.

9. (Withdrawn-currently amended) A method for planarizing a semiconductor wafer comprising:

applying an aqueous chemical mechanical planarizing composition to the wafer, wherein the composition comprises 0.05 to 15 wt% abrasive; 0.1 to 10 wt% oxidizing agent; and 0.0025 to 2 wt% of benzotriazole; and 0.01 to 5 wt% of a water soluble polymaleic acid~~carboxylic acid~~ polymer, wherein at least one repeat unit of the polymer has at least two carboxylic acid functionalities, and wherein the pH of the chemical mechanical planarizing composition is less than 4 adjusted with an inorganic pH adjusting agent, the inorganic pH adjusting agent including an acid selected from nitric acid, sulfuric acid, hydrochloric acid and phosphoric acid; and

polishing the semiconductor wafer at a pad pressure less than or equal to about 21.7 kPa, wherein the chemical mechanical planarizing composition has a tantalum nitride to copper selectivity of at least eighty percent of copper removal rate.

10. Cancelled.